

SYSTEM AND METHOD FOR BACK-SIDE CONTACT
FOR TRENCH SEMICONDUCTOR DEVICE CHARACTERIZATION

Abstract of the Disclosure

5 A method for forming a back-side contact for a vertical trench device includes grinding a back-side of a semiconductor substrate, milling a trench in the back-side of the semiconductor substrate, wherein a vertical trench fill is exposed, and depositing a conductive material, wherein the

10 conductive material shorts the vertical trench fill to a buried plate. Grinding the back-side of the semiconductor substrate further includes grinding a dimple beneath a portion of the vertical trench device, wherein the trench is milled in the bottom portion of the dimple.

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